

Data Sheet N0664 Rev. B

12TQ200 12TQ200S



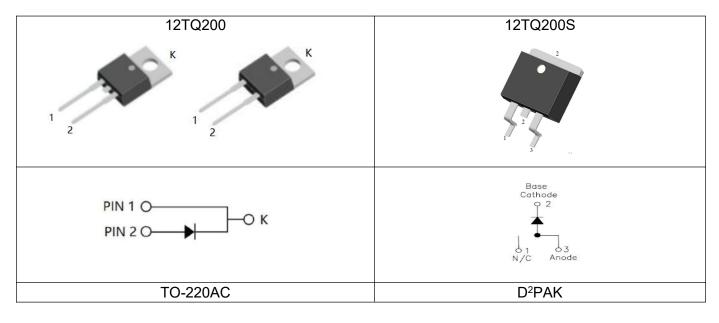
12TQ200/S SCHOTTKY RECTIFIER

Features

- 175℃ T_J operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection



Maximum Ratings(@Tc=25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} Vr	-	200	V
Average Rectified Forward Current	I _{F (AV)}	Tc=122°C, In DC	15	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3ms, Half Sine pulse	276	А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.84	0.92	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.71	0.76	V
Reverse Current *	I _{R1}	@V _R = rated V _R T _J = 25 ℃	0.0001	0.55	mA
	I _{R2}	@V _R = rated V _R T _J = 125 ℃	0.08	7	mA
Junction Capacitance	CT	@V _R = 5V, T _C = 25 ℃ f _{SIG} = 1MHz	270	300	pF
Series Inductance	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

* Pulse width < 300 $\mu s, \ duty \ cycle < 2\%$

Thermal-Mechanical Specifications:

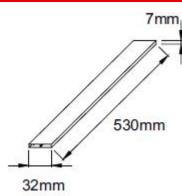
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R _{θJC}	DC operation	2.0	°C/W
Typical Thermal Resistance Case to Heat Sink	R _{0Cs}	Mounting surface, smooth and greased(only for TO-220)	0.50	°C/W
Case Style	TO-220AC D ² PAK			

Tube Specification

Device	Package	Weight	Shipping
12TQ200	TO-220AC	1.8g	50pcs / tube
12TQ200S	D ² PAK	1.85g	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

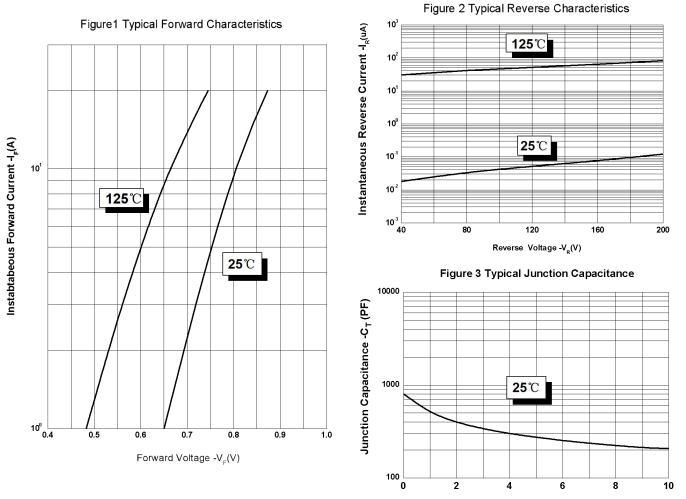
Tube Specification(TO-220AC)



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Ratings and Characteristics Curves



Reverse Voltage - $V_{R}(V)$

12TQ200

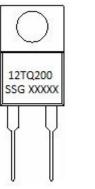
RoHS

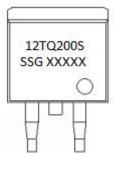
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Po



Marking Diagram



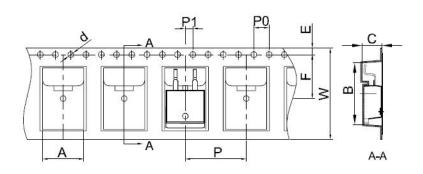


Where XXXXX is YYWWL

YY = Year WW = Week L = Lot Number
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tions: Molding resin Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK



Symbol	Millimeters		
	Min.	Max.	
А	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	



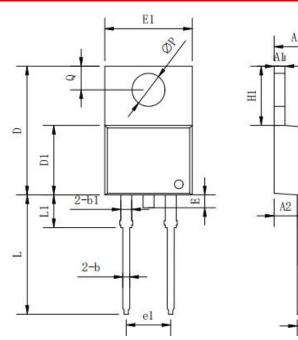




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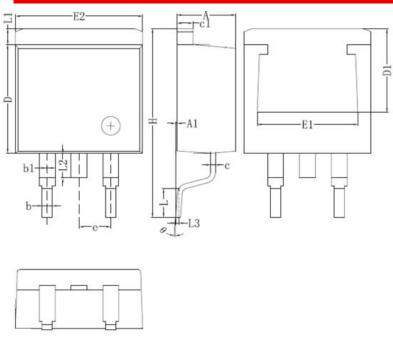


Mechanical Dimensions TO-220AC



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
Α	3.56	-	4.83
A1	0.51	-	1.4
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
С	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	-	-	1.78
E1	9.65	10.16	10.67
e1	-	5.08	-
H1	5.84	-	6.86
L	12.7	-	14.73
L1	-	-	6.35
ΦΡ	-	3.56	-
Q	2.54	-	3.43

Mechanical Dimensions D²PAK



Symbol	Dimensions i	n millimeters	
Symbol	Min.	Max.	
А	4.06	4.83	
A1	0	0.26	
b	0.51	0.99	
b1	1.14	1.78	
С	0.31	0.74	
c1	1.14	1.65	
D	8.38	9.65	
D1	6.4		
E1	6.22		
E2	9.65	10.67	
е	2.54BSC		
Н	14.6	15.88	
L	1.78	2.8	
L1	-	1.68	
L2	-	2.2	
L3	0.255BSC		
Θ	0	8°	

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